

T-440-07-05

MC54/74HC574

Octal 3-State Noninverting D Flip-Flop

High-Performance Silicon-Gate CMOS

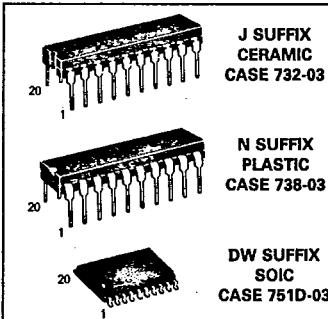
The MC54/74HC574 is identical in pinout to the LS574. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

Data meeting the setup time is clocked to the outputs with the rising edge of the Clock. The Output Enable input does not affect the states of the flip-flops, but when Output Enable is high, all device outputs are forced to the high-impedance state. Thus, data may be stored even when the outputs are not enabled.

The HC574 is identical in function to the HC374 but has the flip-flop inputs on the opposite side of the package from the outputs to facilitate PC board layout.

The HC574 is the noninverting version of the HC564.

- Output Drive Capability: 15 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2 to 6 V
- Low Input Current: 1 μ A
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- Chip Complexity: 266 FETs or 66.5 Equivalent Gates

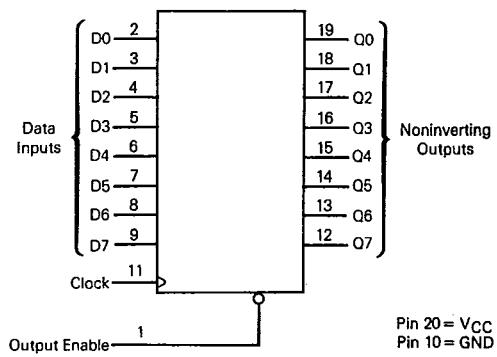


ORDERING INFORMATION

MC74HCXXXN	Plastic
MC54HCXXXJ	Ceramic
MC74HCXXXDW	SOIC

$T_A = -55^\circ$ to 125°C for all packages.
Dimensions in Chapter 7.

LOGIC DIAGRAM



PIN ASSIGNMENT

Output Enable	1	20	V _{CC}
D0	2	19	Q0
D1	3	18	Q1
D2	4	17	Q2
D3	5	16	Q3
D4	6	15	Q4
D5	7	14	Q5
D6	8	13	Q6
D7	9	12	Q7
GND	10	11	Clock

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FUNCTION TABLE

Output Enable	Inputs		Output
	Clock	D	
L	/	H	H
L	/	L	L
L	L, H, /	X	no change
H	X	X	Z

X = don't care
Z = high impedance

MAXIMUM RATINGS*

Symbol	Parameter	Value	Unit
V_{CC}	DC Supply Voltage (Referenced to GND)	-0.5 to +7.0	V
V_{in}	DC Input Voltage (Referenced to GND)	-1.5 to $V_{CC}+1.5$	V
V_{out}	DC Output Voltage (Referenced to GND)	-0.5 to $V_{CC}+0.5$	V
I_{in}	DC Input Current, per Pin	± 20	mA
I_{out}	DC Output Current, per Pin	± 35	mA
I_{CC}	DC Supply Current, V_{CC} and GND Pins	± 75	mA
P_D	Power Dissipation In Still Air, Plastic or Ceramic DIP or SOIC Package	750 500	mW
T_{stg}	Storage Temperature	-65 to +150	°C
T_L	Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP or SOIC Package) (Ceramic DIP)	260 300	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range $GND \leq (V_{in} \text{ or } V_{out}) \leq V_{CC}$. Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

*Maximum Ratings are those values beyond which damage to the device may occur. Functional operation should be restricted to the Recommended Operating Conditions.

†Derating — Plastic DIP: -10 mW/°C from 65° to 125°C

Ceramic DIP: -10 mW/°C from 100° to 125°C

SOIC Package: -7 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 4.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit	
V_{CC}	DC Supply Voltage (Referenced to GND)	2.0	6.0	V	
V_{in}, V_{out}	DC Input Voltage, Output Voltage (Referenced to GND)	0	V_{CC}	V	
T_A	Operating Temperature, All Package Types	-55	+125	°C	
t_r, t_f	Input Rise and Fall Time (Figure 1)	$V_{CC}=2.0\text{ V}$ $V_{CC}=4.5\text{ V}$ $V_{CC}=6.0\text{ V}$	0 0 0	1000 500 400	ns

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

Symbol	Parameter	Test Conditions	V_{CC} V	Guaranteed Limit			Unit
				25°C to -55°C	$\leq 85^\circ\text{C}$	$\leq 125^\circ\text{C}$	
V_{IH}	Minimum High-Level Input Voltage	$V_{out}=0.1\text{ V}$ or $V_{CC}-0.1\text{ V}$ $ I_{out} \leq 20\text{ }\mu\text{A}$	2.0 4.5 6.0	1.5 3.15 4.2	1.5 3.15 4.2	1.5 3.15 4.2	V
V_{IL}	Maximum Low-Level Input Voltage	$V_{out}=0.1\text{ V}$ or $V_{CC}-0.1\text{ V}$ $ I_{out} \leq 20\text{ }\mu\text{A}$	2.0 4.5 6.0	0.3 0.9 1.2	0.3 0.9 1.2	0.3 0.9 1.2	V
V_{OH}	Minimum High-Level Output Voltage	$V_{in}=V_{IH}$ or V_{IL} $ I_{out} \leq 20\text{ }\mu\text{A}$	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
		$V_{in}=V_{IH}$ or V_{IL} $ I_{out} \leq 6.0\text{ mA}$ $ I_{out} \leq 7.8\text{ mA}$	4.5 6.0	3.98 5.48	3.84 5.34	3.70 5.20	
V_{OL}	Maximum Low-Level Output Voltage	$V_{in}=V_{IH}$ or V_{IL} $ I_{out} \leq 20\text{ }\mu\text{A}$	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		$V_{in}=V_{IH}$ or V_{IL} $ I_{out} \leq 6.0\text{ mA}$ $ I_{out} \leq 7.8\text{ mA}$	4.5 6.0	0.26 0.26	0.33 0.33	0.40 0.40	
I_{in}	Maximum Input Leakage Current	$V_{in}=V_{CC}$ or GND	6.0	± 0.1	± 1.0	± 1.0	μA
I_{OZ}	Maximum Three-State Leakage Current	Output in High-Impedance State $V_{in}=V_{IL}$ or V_{IH} $V_{out}=V_{CC}$ or GND	6.0	± 0.5	± 5.0	± 10.0	μA
I_{CC}	Maximum Quiescent Supply Current (per Package)	$V_{in}=V_{CC}$ or GND $I_{out}=0\text{ }\mu\text{A}$	6.0	8	80	160	μA

NOTE: Information on typical parametric values can be found in Chapter 4.

AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input $t_r = t_f = 6 \text{ ns}$)

Symbol	Parameter	V_{CC} V	Guaranteed Limit			Unit
			25°C to -55°C	$\le 85^\circ\text{C}$	$\le 125^\circ\text{C}$	
f_{max}	Maximum Clock Frequency (50% Duty Cycle) (Figures 1 and 4)	2.0	6.0	4.8	4.0	MHz
		4.5	30	24	20	
		6.0	35	28	24	
$t_{PLH},$ t_{PHL}	Maximum Propagation Delay, Clock to Q (Figures 1 and 4)	2.0	175	220	265	ns
		4.5	35	44	53	
		6.0	30	37	45	
$t_{PLZ},$ t_{PHZ}	Maximum Propagation Delay, Output Enable to Q (Figures 2 and 5)	2.0	150	190	225	ns
		4.5	30	38	45	
		6.0	26	33	38	
$t_{PZL},$ t_{PZH}	Maximum Propagation Delay, Output Enable to Q (Figures 2 and 5)	2.0	150	190	225	ns
		4.5	30	38	45	
		6.0	26	33	38	
$t_{TLH},$ t_{THL}	Maximum Output Transition Time, Any Output (Figures 1 and 4)	2.0	60	75	90	ns
		4.5	12	15	18	
		6.0	10	13	15	
C_{in}	Maximum Input Capacitance	--	10	10	10	pF
C_{out}	Maximum Three-State Output Capacitance (Output in High-Impedance State)	--	15	15	15	pF

NOTES:

1. For propagation delays with loads other than 50 pF, see Chapter 4.
2. Information on typical parametric values can be found in Chapter 4.

CPD	Power Dissipation Capacitance (Per Flip-Flop) Used to determine the no-load dynamic power consumption: $P_D = CPD V_{CC}^2 f + I_{CC} V_{CC}$ For load considerations, see Chapter 4.	Typical @ 25°C , $V_{CC} = 5.0 \text{ V}$			pF
		25°C to -55°C	$\le 85^\circ\text{C}$	$\le 125^\circ\text{C}$	
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TIMING REQUIREMENTS (Input $t_r = t_f = 6 \text{ ns}$)

Symbol	Parameter	V_{CC} V	Guaranteed Limit			Unit
			25°C to -55°C	$\le 85^\circ\text{C}$	$\le 125^\circ\text{C}$	
t_{su}	Minimum Setup Time, Data to Clock (Figure 3)	2.0	100	125	150	ns
		4.5	20	25	30	
		6.0	17	21	26	
t_h	Minimum Hold Time, Clock to Data (Figure 3)	2.0	5	5	6	ns
		4.5	5	5	5	
		6.0	5	5	5	
t_w	Minimum Pulse Width, Clock (Figure 1)	2.0	80	100	120	ns
		4.5	16	20	24	
		6.0	14	17	20	
t_r, t_f	Maximum Input Rise and Fall Times (Figure 1)	2.0	1000	1000	1000	ns
		4.5	500	500	500	
		6.0	400	400	400	

NOTE: Information on typical parametric values can be found in Chapter 4.

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SWITCHING WAVEFORMS

FIGURE 1

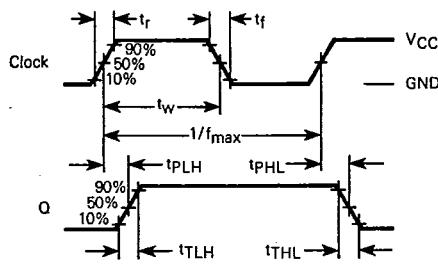


FIGURE 2

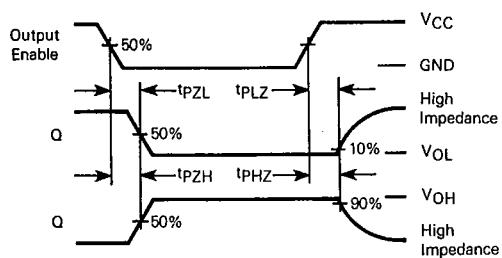


FIGURE 3

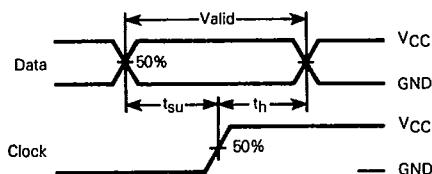
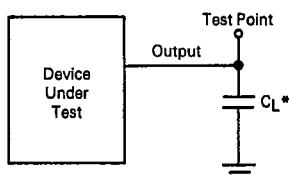
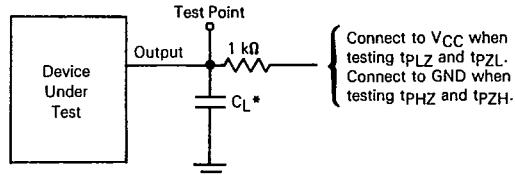


FIGURE 4 — TEST CIRCUIT



* Includes all probe and jig capacitance.

FIGURE 5 — TEST CIRCUIT

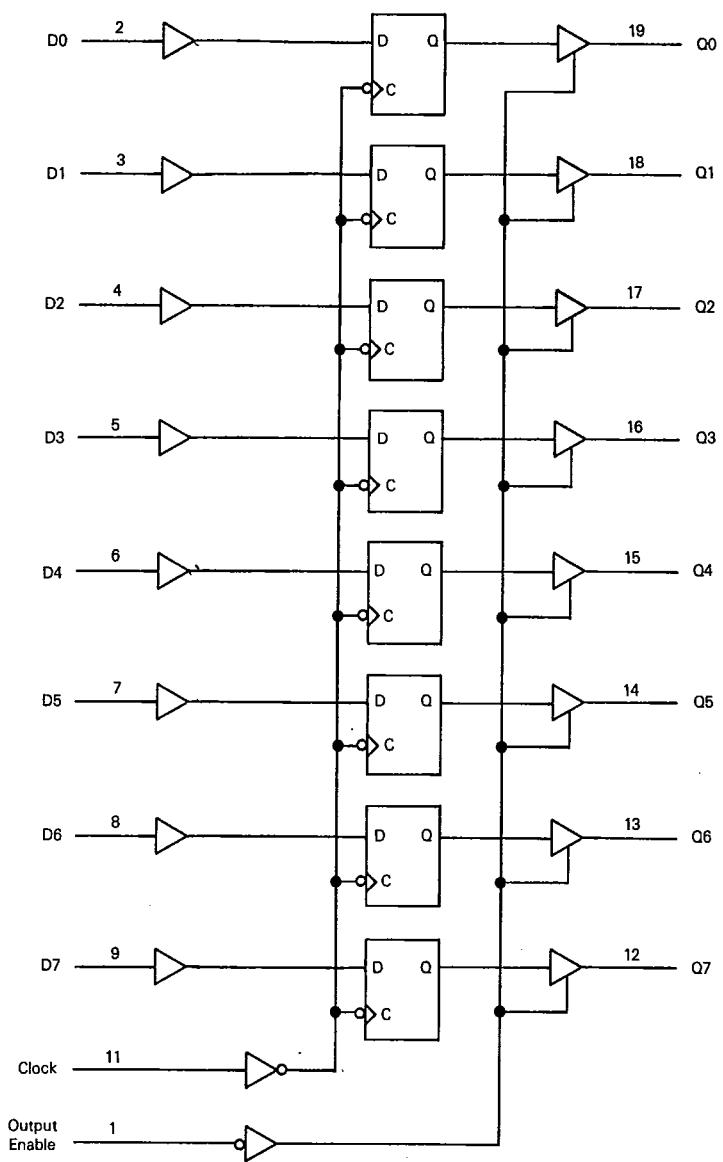


* Includes all probe and jig capacitance.

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EXPANDED LOGIC DIAGRAM



MOTOROLA HIGH-SPEED CMOS LOGIC DATA